

# NME6001H-R1 GaN TRANSISTOR

Document Number:  
NME6001H-R1  
Preliminary Datasheet V1.0

## Gallium Nitride 28V 10W, RF Power Transistor

### Description

The NME6001H-R1 is a 10W, unmatched GaN HEMT, designed for multiple applications with frequencies up to 6GHz.

There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical performance (on Innogration fixture with device soldered)

$V_{DD}=28V$ ,  $I_{DQ}=60mA$ , Pulsed CW,

Frequency(MHz)	Gp (dB)	P <sub>SAT</sub> (W)	Efficiency (%)
5600	10	15	61



### Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

### Important Note: Proper Biasing Sequence for GaN HEMT Transistors

#### Turning the device ON

1. Set VGS to the pinch-off (VP) voltage, typically -5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

#### Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically -5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

**Table 1. Maximum Ratings (Not simultaneous, TC = 25°C unless otherwise noted)**

Rating	Symbol	Value	Unit
Drain--Source Voltage	$V_{DSS}$	150	Vdc
Gate--Source Voltage	$V_{GS}$	-10,+2	Vdc
Operating Voltage	$V_{DD}$	40	Vdc
Maximum Forward Gate Current	$I_{gmax}$	3	mA
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_c$	+150	°C
Operating Junction Temperature(See note 1)	$T_J$	+200	°C
Total Device Power Dissipation (Derated above 25°C,see note 2)	$P_{diss}$	20	W

1. Continuous operation at maximum junction temperature will affect MTTF
2. Bias Conditions should also satisfy the following expression:  $P_{diss} < (T_j - T_c) / R_{JC}$  and  $T_c = T_{case}$

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_c=85^\circ C$ , $T_J=200^\circ C$ , DC Power Dissipation(See note 1)	$R_{\theta JC-DC}$	9	C/W

1.  $R_{\theta JC-DC}$  is tested at only DC condition, it is related to the highest thermal resistance value among all test conditions. It might be differently lower in different RF operation conditions like CW signal ,pulsed RF signal etc.

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**Table 3. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

**DC Characteristics**

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS}=-8\text{V}; I_{DS}=3\text{mA}$	$V_{DSS}$	150			V
Gate Threshold Voltage	$V_{DS} = 28\text{V}, I_D = 3\text{mA}$	$V_{GS(th)}$		-2.7		V
Gate Quiescent Voltage	$V_{DS} = 28\text{V}, I_{DS}=60\text{mA}$ , Measured in Functional Test	$V_{GS(Q)}$	---	-2.3	---	V

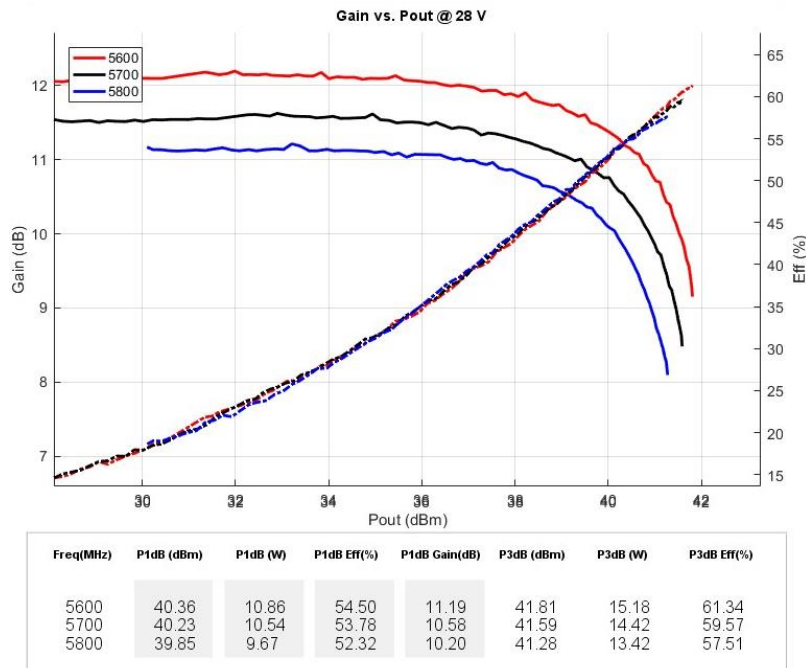
**Functional Tests (In Innogration Test Fixture, 50 ohm system) :**  $V_{DD} = 28\text{Vdc}$ ,  $I_{DQ} = 60\text{mA}$ ,  $f = 5600\text{MHz}$ , Pulsed CW

Characteristic	Symbol	Min	Typ	Max	Unit
Power Gain@P <sub>sat</sub>	G <sub>p</sub>	9.5	10		dB
Drain Efficiency@P <sub>sat</sub>	Eff		60		%
Saturated Power	P <sub>sat</sub>	12	15		W
Input Return Loss	IRL		-5		dB
Mismatch stress at all phases(No device damage)	VSWR		10:1		Ψ

## TYPICAL CHARACTERISTICS

**Figure 1. Power gain and drain efficiency as function of average load power**

$V_{DD}=28\text{V}, I_{DQ}=60\text{mA}$ , Pulsed condition: 12us, 10%

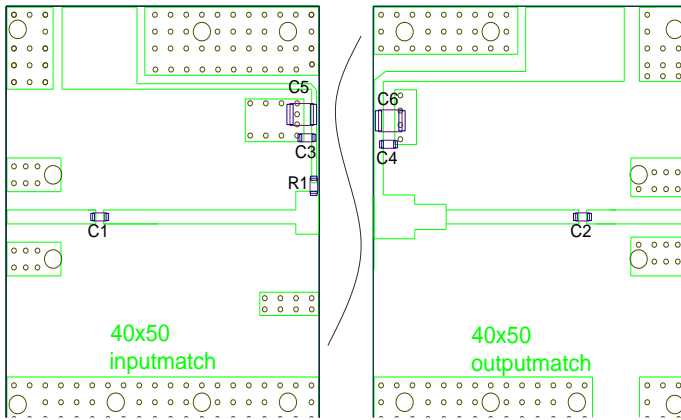


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Figure 2. test fixture ,BOM and layout (Layout file upon request,)

PCB: 30 Mil Rogers 4350B



Designator	Comment	Description	Footprint	Quantity
C1, C2, C3, C4	3.3pF	ATC600F	0805	4
C5, C6	10uF/50V	X7R	1210	2
R1	10R	Resistor	0603	1

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## Package Outline

Flanged ceramic package; 2 leads

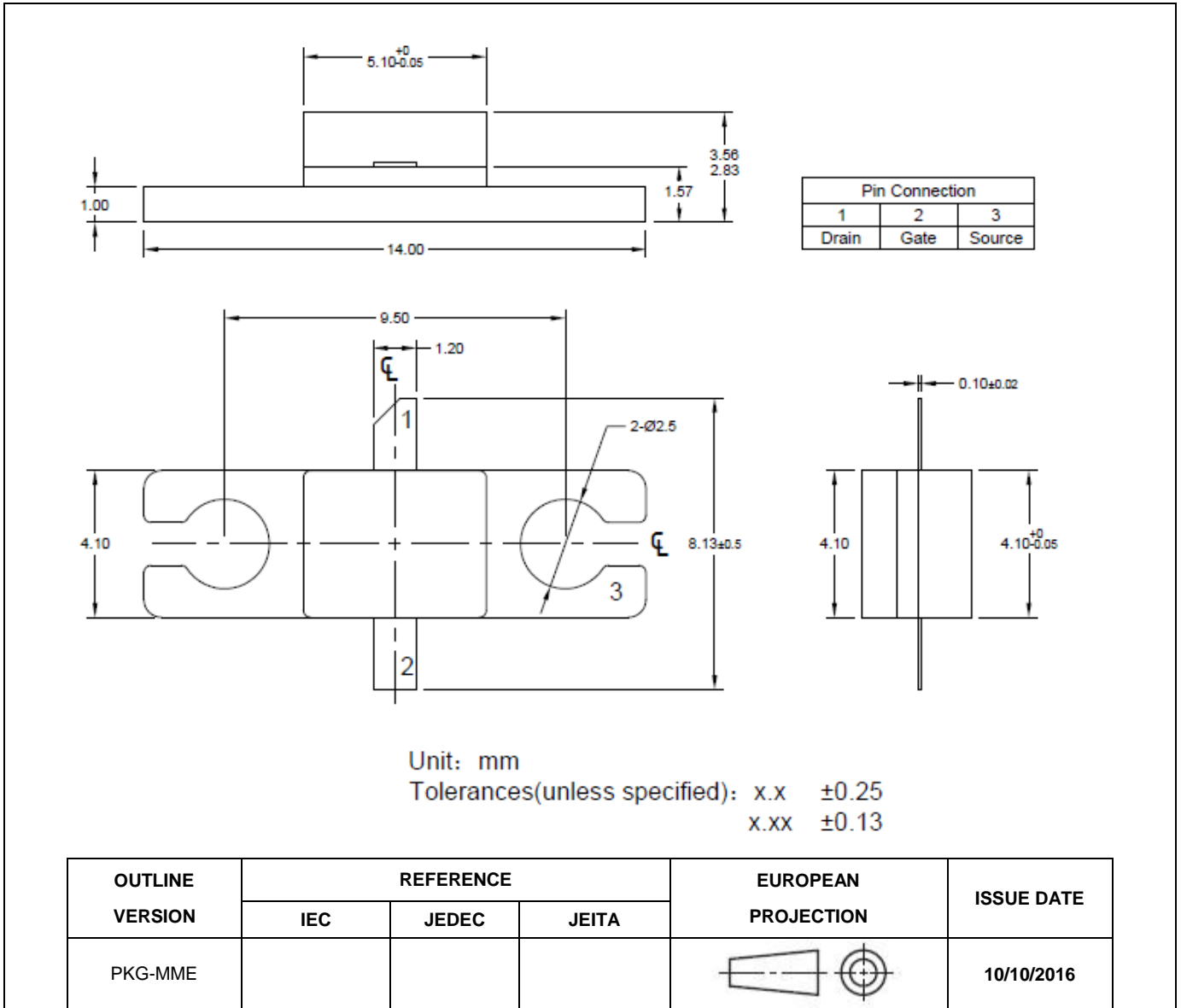


Figure 1. Package Outline PKG-MME

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## Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2019/2/19	V1.0	Preliminary datasheet creation

### Notice

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